

N-Channel 80 V (D-S) MOSFET

DESCRIPTION

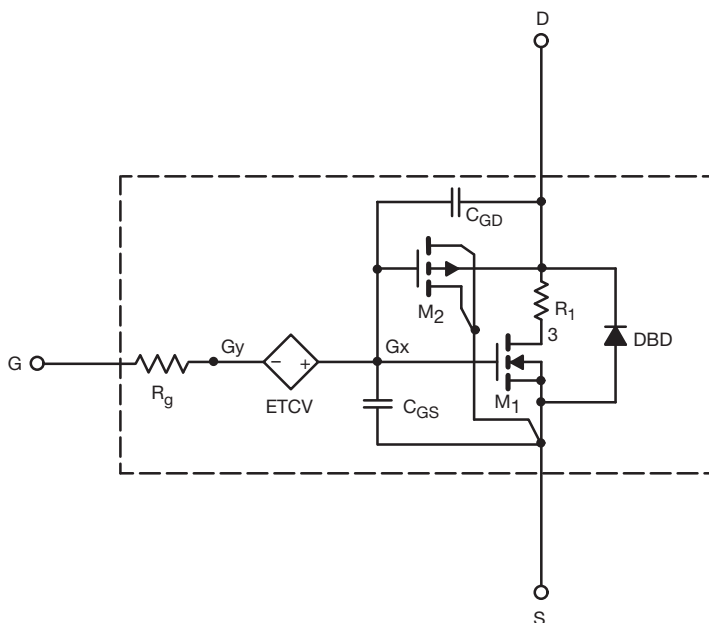
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



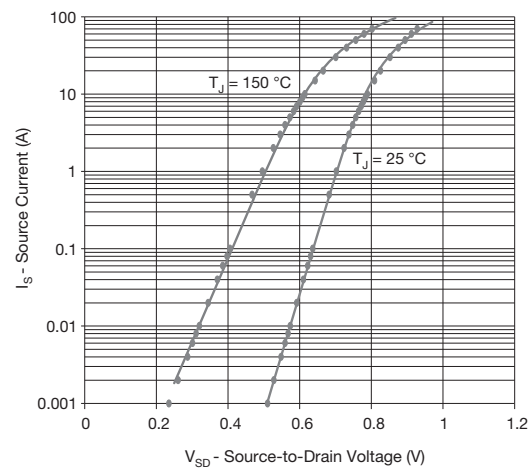
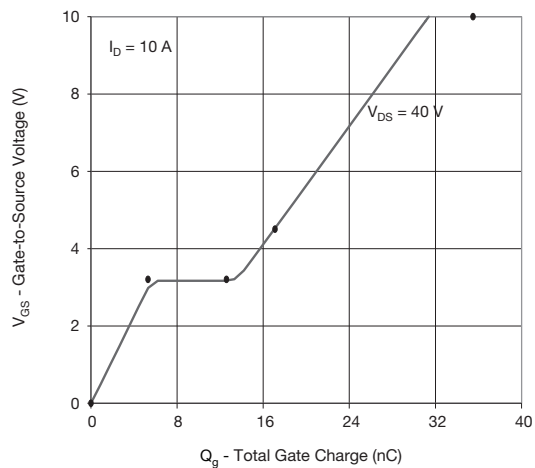
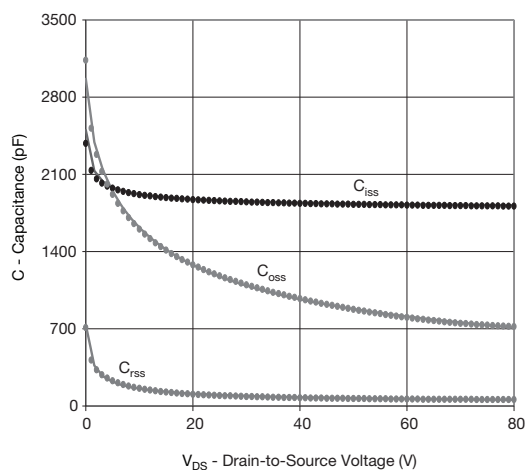
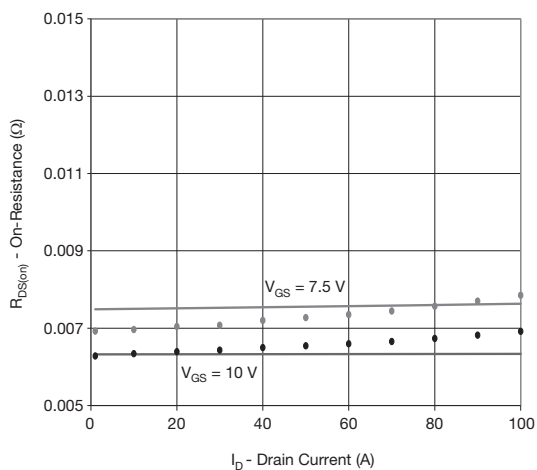
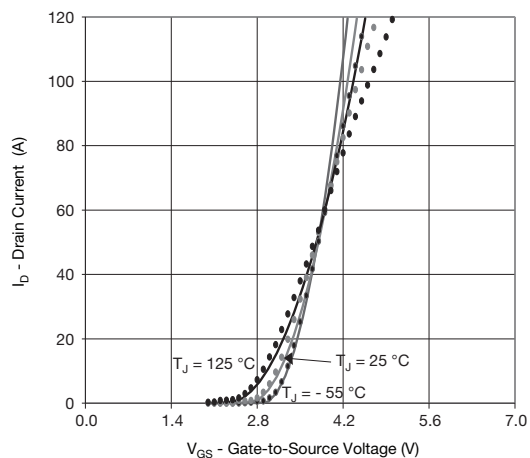
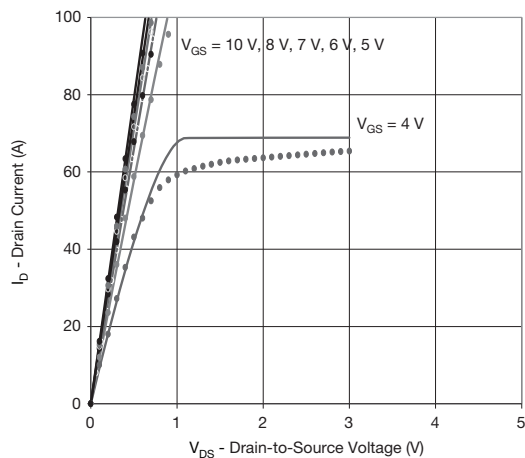
| SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted) | | | | | |
|---|--------------|--|----------------|---------------|----------|
| PARAMETER | SYMBOL | TEST CONDITIONS | SIMULATED DATA | MEASURED DATA | UNIT |
| Static | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$ | 2.1 | - | V |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$, $I_D = 20\text{ A}$ | 0.0063 | 0.0064 | Ω |
| | | $V_{GS} = 6\text{ V}$, $I_D = 15\text{ A}$ | 0.0075 | 0.0070 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 10\text{ V}$, $I_D = 20\text{ A}$ | 53 | 60 | S |
| Diode Forward Voltage | V_{SD} | $I_S = 10\text{ A}$ | 0.76 | 0.76 | V |
| Dynamic ^b | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 40\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | 1840 | 1855 | pF |
| Output Capacitance | C_{oss} | | 969 | 950 | |
| Reverse Transfer Capacitance | C_{rss} | | 79 | 76 | |
| Total Gate Charge | Q_g | $V_{DS} = 40\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$ | 32 | 35.5 | nC |
| Gate-Source Charge | Q_{gs} | $V_{DS} = 40\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$ | 17 | 17.1 | |
| Gate-Drain Charge | Q_{gd} | | 5.3 | 5.3 | |
| | | | 7.3 | 7.3 | |

Notesa. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.

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